

High-Power Module Silicon Carbide N-Channel MOSFET

# MG600Q2YMS3

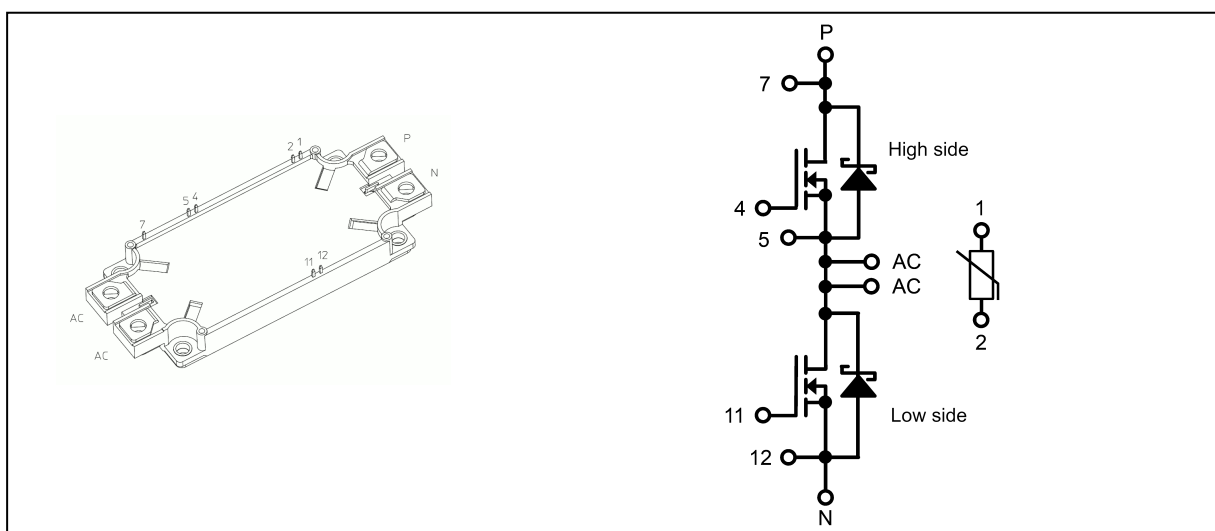
## 1. Applications

- High-Power Switching
- Motor Controllers (including rail traction)

## 2. Features

- (1)  $V_{DSS} = 1200\text{ V}$ ,  $I_D = 600\text{ A}$  All SiC MOSFET Module(Low loss & High speed switching)
- (2) Low stray inductance, low thermal resistance, maximum  $T_{ch} = 150\text{ }^\circ\text{C}$ , built in temperature sensor.
- (3) Enhancement mode.
- (4) Electrodes are isolated from case.

## 3. Packaging and Internal Circuit



(Note 1):P and N terminal should use one screw fastened in each and AC terminal should use two screws fastened.

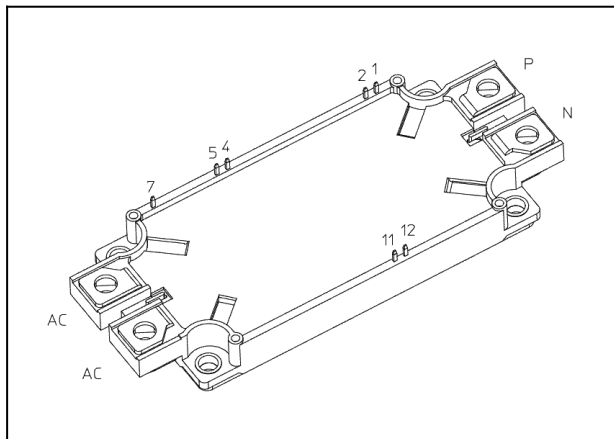
(Note 2):When the thermistor is not used, pin 1 and pin 2 should be electrically connected to pin 12.

Start of commercial production

2021-11

## 4. Terminal

Symbol & No.	Terminal name
P	P(main terminal)
N	N(main terminal)
AC	AC(main terminal)
1	Thermistor
2	Thermistor
4	High side gate
5	High side source sense / Low side drain sense
7	High side drain sense
11	Low side gate
12	Low side source sense



**Fig. 4.1 Terminal image**

### 5. Absolute Maximum Ratings (Note, Note 1)( $T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Note	Test Condition	Rating	Unit
Drain-source voltage	$V_{DSS}$			1200	V
Gate-source voltage	$V_{GSS}$			+ 25 / - 10	V
Drain current (DC)	$I_D$	(Note 2)		600	A
Drain current (pulsed)	$I_{DP}$	(Note 2)		1200	A
Drain power dissipation	$P_D$	(Note 2)		2000	W
Source current (DC)	$I_S$	(Note 2)		600	A
Source current (pulsed)	$I_{SP}$	(Note 2)		1200	A
Channel temperature	$T_{ch}$			150	$^\circ\text{C}$
Storage temperature	$T_{stg}$			-40 - 150	$^\circ\text{C}$
Isolation voltage	$V_{isol}$		AC , 60 s	4000	Vrms
Isolation voltage (thermistor terminal-other terminal)	$V_{isol(therm)}$		AC , 60 s	4000	Vrms
Mounting torque	TOR	(Note 3)	Main terminal: M6	4.5	N · m
		(Note 4)	Mounting: M5	3.5	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: refer to the application notes.

Note 2: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

Note 3: The recommended tightening torque for the main terminal (M6) is  $4.0\text{ N} \cdot \text{m}$ .

Note 4: The recommended tightening torque for installation (M5) is  $3.0\text{ N} \cdot \text{m}$ .

### 6. Thermal-resistance

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
Thermal resistance (channel-to-case)	$R_{th(ch-c)}$	(Note 1)	—	—	0.060	K/W
Thermal resistance (case-to-fin)	$R_{th(c-f)}$	(Note 2)	—	0.013	—	K/W

Note 1: The value per half a module.

Note 2: The value per module.

Apply  $50\text{ }\mu\text{m}$  of  $3\text{ W/m} \cdot \text{K}$  grease between the case and fin while taking care not to create a void, and tighten to the recommended torque before use.

### 7. Electrical Characteristics (Note)(T<sub>c</sub> = 25 °C unless otherwise specified)

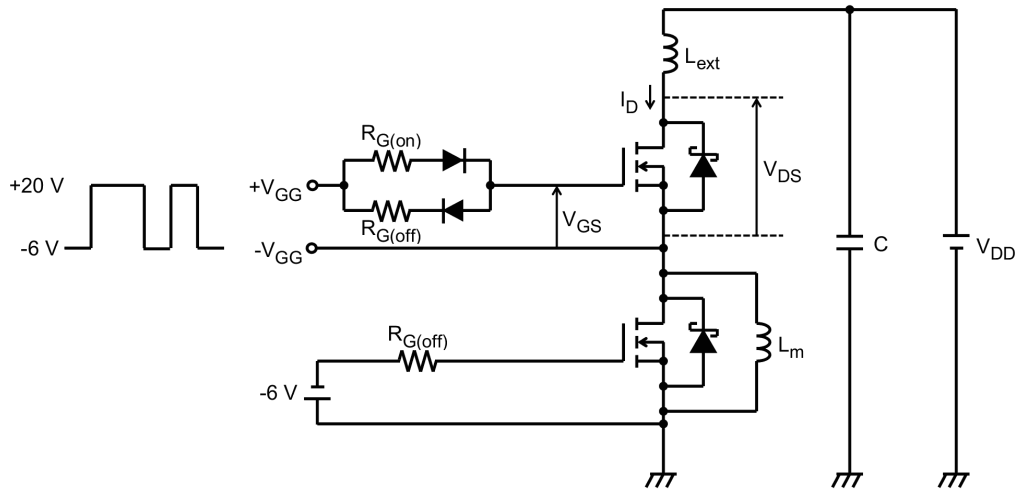
Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit	Fig.
Gate-source leakage current	I <sub>GSS</sub>		V <sub>GS</sub> = +25 V / -10 V, V <sub>DS</sub> = 0 V	—	—	±30	nA	—
Drain-source cut-off current	I <sub>DSS</sub>		V <sub>DS</sub> = 1200V, V <sub>GS</sub> = 0 V	—	—	250	μA	—
Gate threshold voltage	V <sub>th</sub>	(Note3)	I <sub>D</sub> = 0.6 A, V <sub>DS</sub> = 10 V	3.6	4.6	5.6	V	—
Drain-source on-voltage (sense)	V <sub>DS(on) sense</sub>	(Note2)	I <sub>D</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 25 °C	—	0.9	—	V	—
			I <sub>D</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 150 °C	—	1.4	2.1	V	—
Drain-source on-voltage (terminal)	V <sub>DS(on) terminal</sub>	(Note1)	I <sub>D</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 25 °C	—	1.4	—	V	—
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V, f = 10 kHz	—	53	—	nF	—
Switching time (turn-on delay time)	t <sub>d(on)</sub>	(Note)	Inductive load, V <sub>DS</sub> = 600 V, I <sub>D</sub> = 600 A, V <sub>GS</sub> = + 20 V / - 6 V, R <sub>G(on)</sub> = 3.9 Ω, R <sub>G(off)</sub> = 3.9 Ω, T <sub>ch</sub> = 150 °C, L <sub>S</sub> ≈ 40 nH	—	0.23	—	μs	7.1
Switching time (rise time)	t <sub>r</sub>			—	0.10	—	μs	7.2
Switching time (turn-on time)	t <sub>on</sub>			—	0.33	—	μs	7.3
Switching time (turn-off delay time)	t <sub>d(off)</sub>			—	0.48	—	μs	
Switching time (fall time)	t <sub>f</sub>			—	0.07	—	μs	
Switching time (turn-off time)	t <sub>off</sub>			—	0.55	—	μs	
Turn-on switching loss	E <sub>on</sub>			—	25	—	mJ	
Turn-off switching loss	E <sub>off</sub>			—	28	—	mJ	
Source-drain on-voltage (sense)	V <sub>SD(on) sense</sub>	(Note2)	I <sub>S</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 25 °C	—	0.8	—	V	—
			I <sub>S</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 150 °C	—	1.3	1.9	V	—
Source-drain on-voltage (terminal)	V <sub>SD(on) terminal</sub>	(Note1)	I <sub>S</sub> = 600 A, V <sub>GS</sub> = + 20 V, T <sub>ch</sub> = 25 °C	—	1.3	—	V	—
Source-drain off-voltage (sense)	V <sub>SD(off) sense</sub>	(Note2)	I <sub>S</sub> = 600 A, V <sub>GS</sub> = - 6 V, T <sub>ch</sub> = 25 °C	—	1.6	—	V	—
			I <sub>S</sub> = 600 A, V <sub>GS</sub> = - 6 V, T <sub>ch</sub> = 150 °C	—	2.2	3.2	V	—
Source-drain off-voltage (terminal)	V <sub>SD(off) terminal</sub>	(Note1)	I <sub>S</sub> = 600 A, V <sub>GS</sub> = - 6 V, T <sub>ch</sub> = 25 °C	—	2.1	—	V	—
Reverse recovery time	t <sub>rr</sub>	(Note)	Inductive load, I <sub>S</sub> = 600 A, V <sub>R</sub> = 600 V, Drive side R <sub>G(on)</sub> = 3.9 Ω, T <sub>ch</sub> = 150 °C, L <sub>S</sub> ≈ 40 nH	—	45	—	ns	7.4
Reverse recovery loss	E <sub>rr</sub>			—	0.8	—	mJ	7.6
Stray inductance	L <sub>sPN</sub>		P terminal-N terminal	—	12	—	nH	—
Rated NTC resistance	R		T <sub>c</sub> =25 °C	3.5	5.0	6.5	kΩ	—
			T <sub>c</sub> =150 °C	125	165	205	Ω	—
NTC B value	B		T <sub>NTC</sub> = 25 - 150 °C	—	3375	—	K	—

Note: L<sub>s</sub> is a sum of (L<sub>sPN</sub>) and (L<sub>ext</sub>). (L<sub>ext</sub> is shown in Fig.7.1, 7.2, 7.4, 7.5)

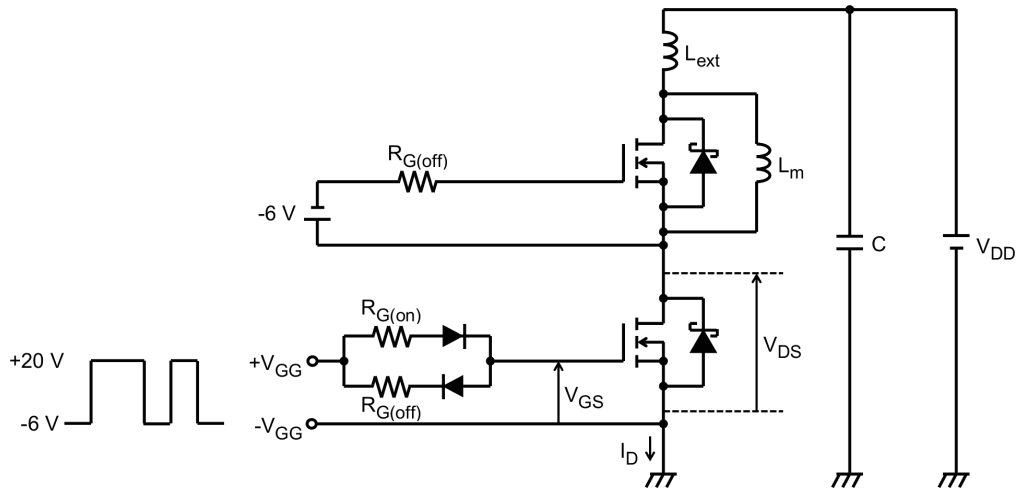
Note1: The values are when two AC terminals are connected.

Note2: The values are measured between drain sense and source sense.

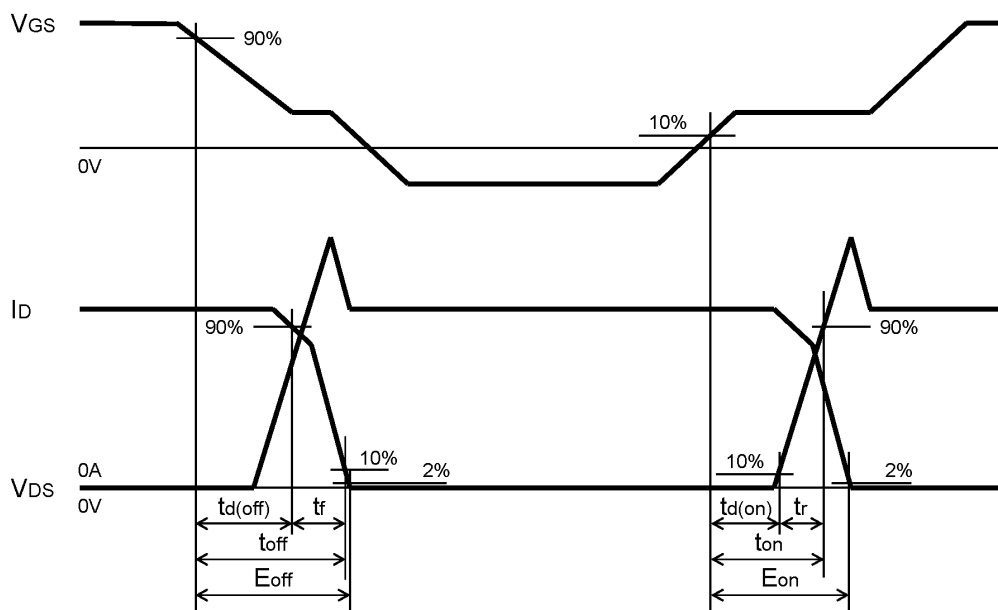
Note3: Gate-source voltage (-10V) is applied 5ms before measurement.



**Fig. 7.1 Inductive Load Switching Test Circuit (High side Switching)**



**Fig. 7.2 Inductive Load Switching Test Circuit (Low side Switching)**



**Fig. 7.3 Timing Chart (MOSFET part)**

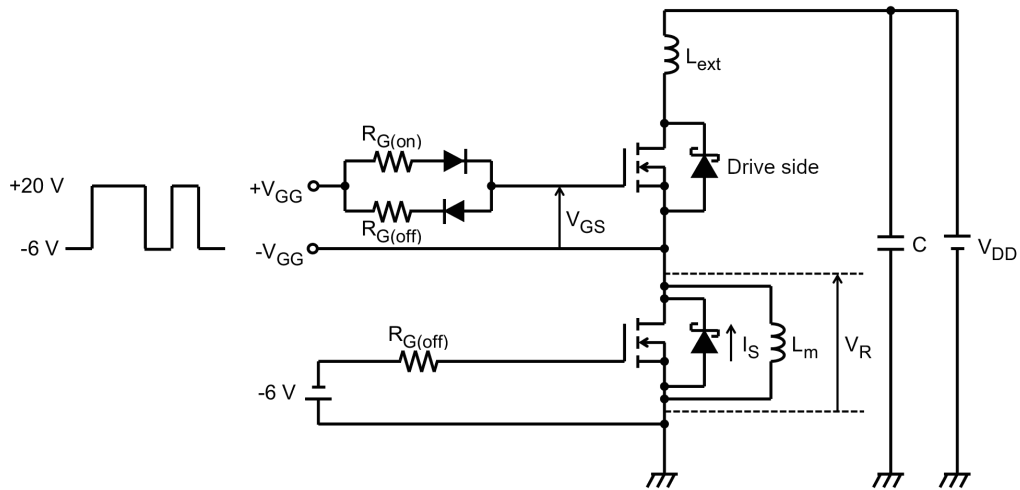


Fig. 7.4 Inductive Load Reverse Recovery Test Circuit (High side Switching)

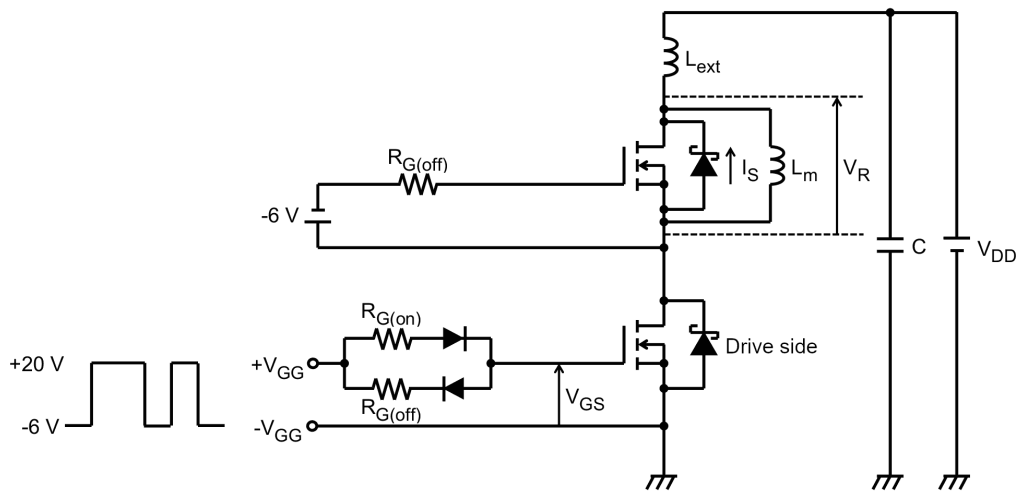


Fig. 7.5 Inductive Load Reverse Recovery Test Circuit (Low side Switching)

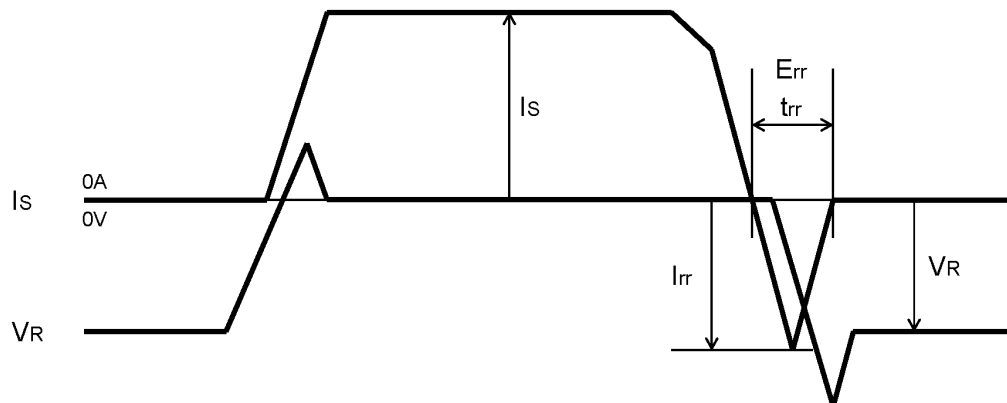
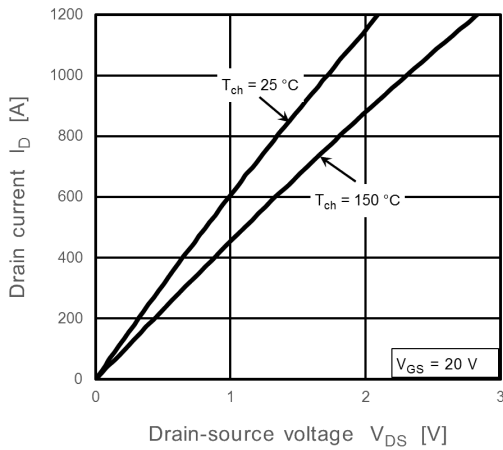
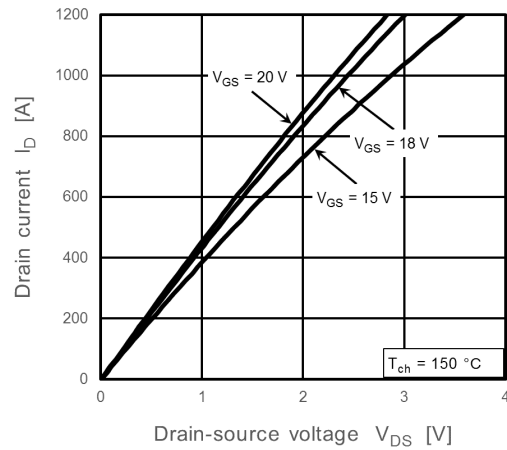


Fig. 7.6 Timing Chart (Diode part)

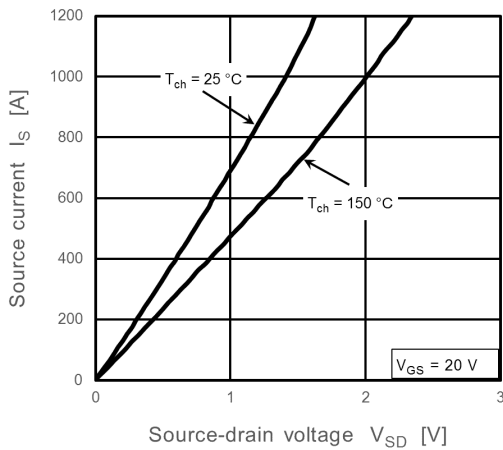
### 8. Characteristics Curves



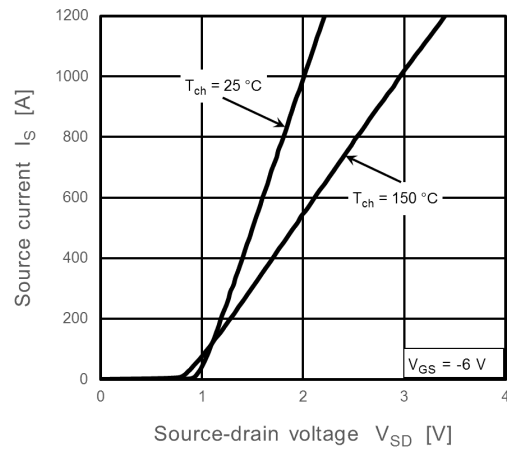
**Fig. 8.1  $I_D - V_{DS}$ (Note 1)**



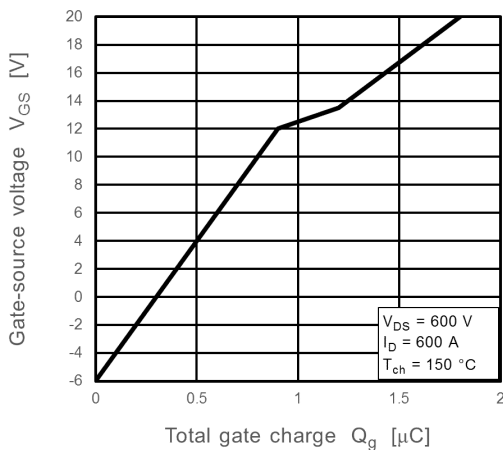
**Fig. 8.2  $I_D - V_{DS}$ (Note 1)**



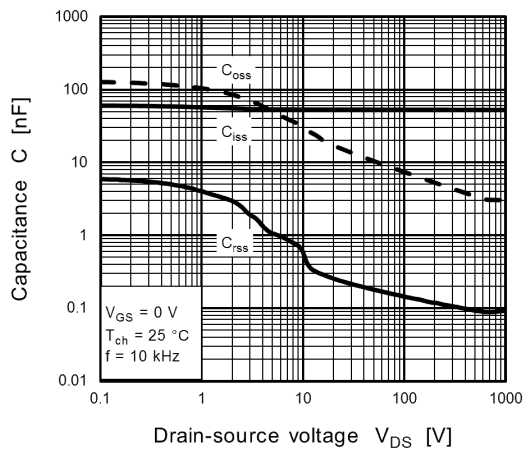
**Fig. 8.3  $I_S - V_{SD}$ (Note 1)**



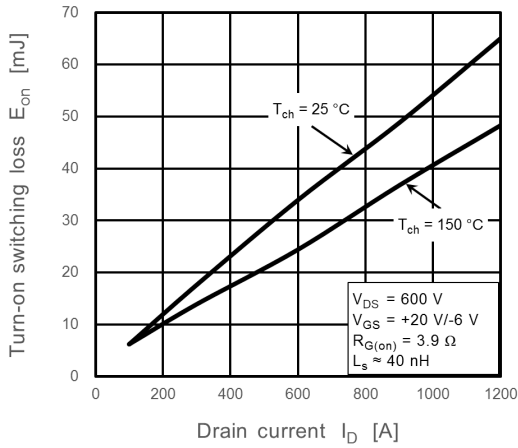
**Fig. 8.4  $I_S - V_{SD}$ (Note 1)**



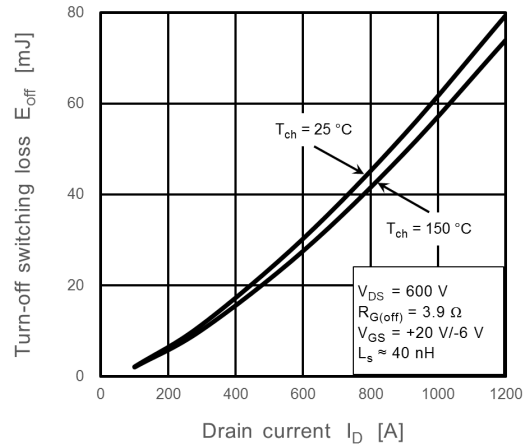
**Fig. 8.5  $V_{GS} - Q_g$**



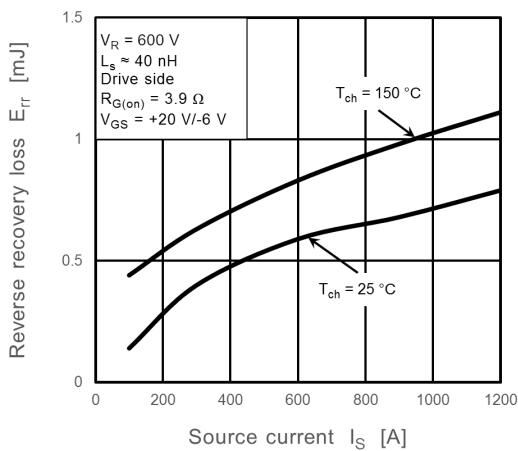
**Fig. 8.6  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$**



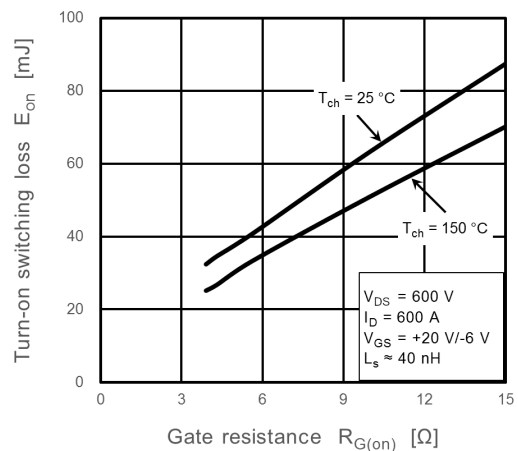
**Fig. 8.7  $E_{on} - I_D$**



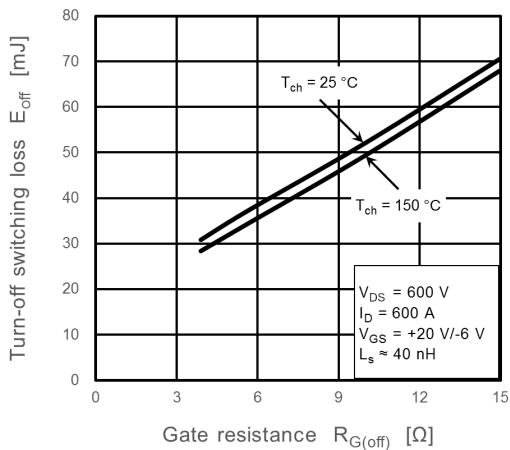
**Fig. 8.8  $E_{off} - I_D$**



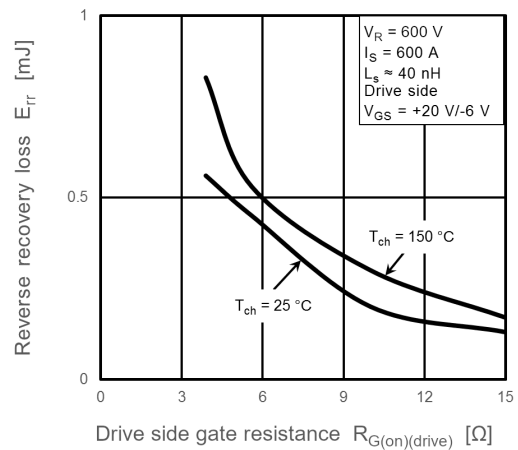
**Fig. 8.9  $E_{rr} - I_S$**



**Fig. 8.10  $E_{on} - R_{G(on)}$**

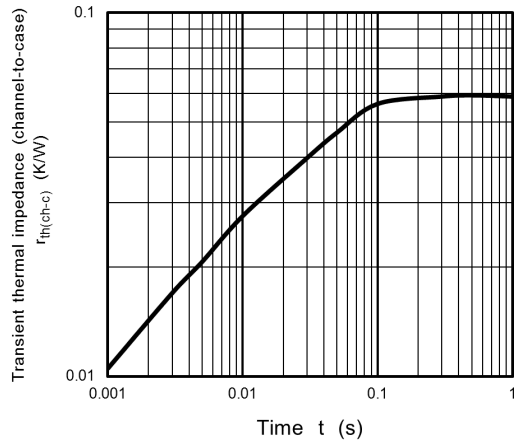


**Fig. 8.11  $E_{off} - R_{G(off)}$**

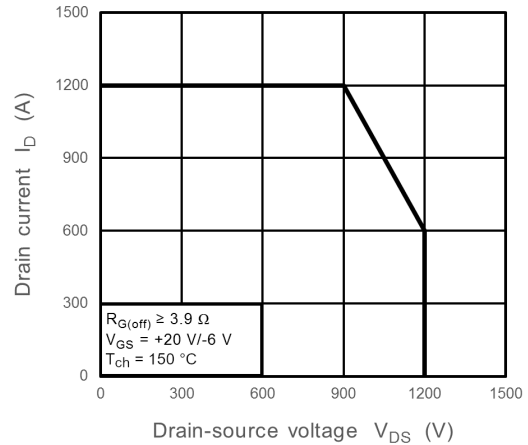


**Fig. 8.12  $E_{rr} - R_{G(on)}$**





**Fig. 8.13  $R_{th(ch-c)} - t$   
(Guaranteed Maximum)**



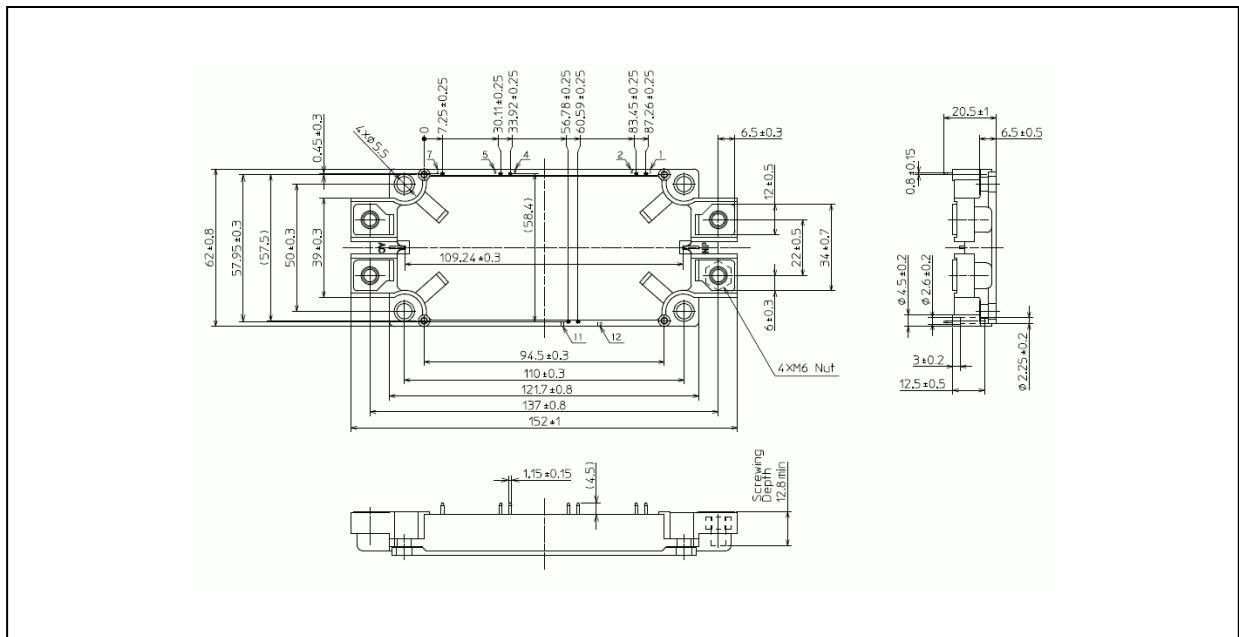
**Fig. 8.14 Reverse bias safe operating area  
(RBSOA)  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Note1: Source - drain voltage and Drain - source voltage are measured at sense terminals.

### Package Dimensions

Unit: mm



Weight: 350 g (typ.)

Package Name(s)
TOSHIBA: 2-153A1A

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